

## Silicon NPN Power Transistors

2SC3153

## DESCRIPTION

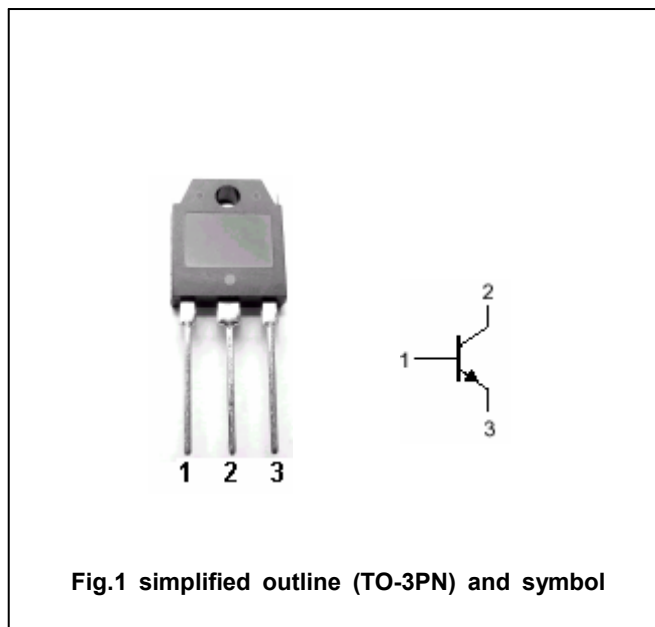
- With TO-3PN package
- High breakdown voltage ( $V_{CBO} \geq 900V$ )
- Fast switching speed
- Wide ASO □ Safe Operating Area □

## APPLICATIONS

- 800V/6A switching regulator applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings ( $T_a = 25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	900	V
$V_{CEO}$	Collector-emitter voltage	Open base	800	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		6	A
$I_{CM}$	Collector current-peak		20	A
$I_B$	Base current		3	A
$P_C$	Collector power dissipation	$T_C = 25^\circ C$	100	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA ; R_{BE}=\infty$	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	900			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=3A ; I_B=0.6A$			2.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=3A ; I_B=0.6A$			1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=800V ; I_E=0$			10	μA
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			10	μA
$h_{FE-1}$	DC current gain	$I_C=0.4A ; V_{CE}=5V$	10		40	
$h_{FE-2}$	DC current gain	$I_C=2A ; V_{CE}=5V$	8			
$C_{OB}$	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		120		pF
$f_T$	Transition frequency	$I_C=0.4A ; V_{CE}=10V$		15		MHz

## Switching times

$t_{on}$	Turn-on time	$I_C=4A ; I_{B1}=0.8A ; I_{B2}=-1.6A$ $R_L=100\Omega, V_{CC}=400V$			1.0	μs
$t_s$	Storage time				3.0	μs
$t_f$	Fall time				0.7	μs

◆  $h_{FE-1}$  classifications

K	L	M
10-20	15-30	20-40

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